

ABSTRACT OF THE DISCLOSURE

In the manufacture of a semiconductor laser device, a low temperature buffer layer is grown on a sapphire substrate at a growth rate of 25 to 30 Å/sec. On the low temperature buffer layer, an n-GaN layer, a anti-crack layer, an n-cladding layer, an n-guide layer, an MQW active layer, a p-carrier blocking layer, a p-guide layer, a p-cladding layer and a p-contact layer are grown in this order. The growth of the low temperature buffer layer at the high growth rate allows a good low temperature buffer layer to be stably provided with good reproducibility. Thus, good crystallinity and electrical characteristics can stably be provided in the above layers.

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